迈诺斯科技

2SC5200

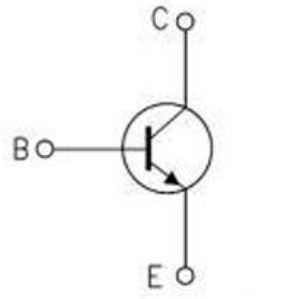
Minos High Power Products

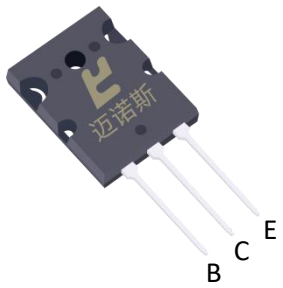
NPN TRANSISTORS

Features:

① Power Amplifier Applications
② Complementary to 2SA1943
③ High collector voltage:V_{CEO}=230V (min)
④ Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.





MINOS TO-3PL

Absolute Maximum Ratings（Tc=25℃）

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	230	V
Collector-emitter voltage		V_{CEO}	230	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I_C	15	A
Base current		I_B	5	A
Collector power dissipation	Tc=25℃	P_C	150	W
Junction temperature		T_j	150	℃
Storage temperature range		T_{STG}	-55~150	℃

Package Marking And Ordering Information：

Ordering Codes	Package	Product Code	Packing
2SC5200	TO-3PL	2SC5200	Tube

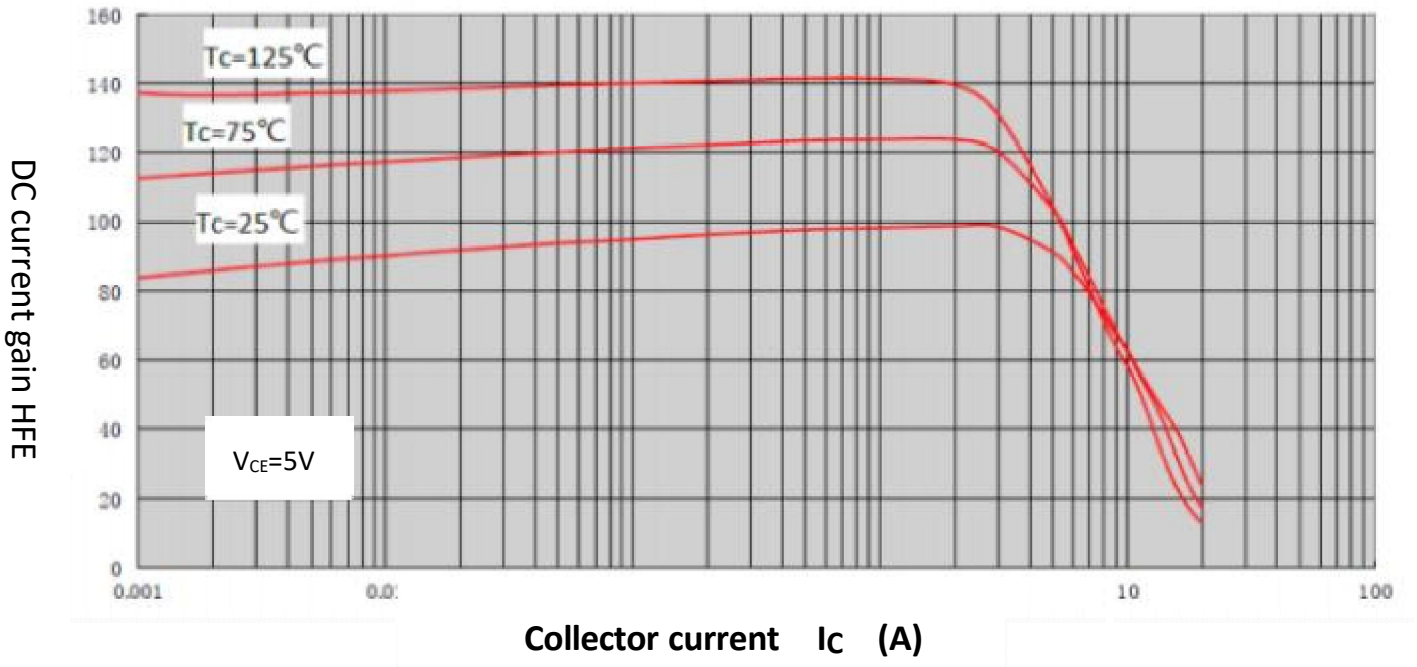
Electrical Characteristics Tc=25℃

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB}=230V; I_E=0			500	uA
Emitter cut-off current	I_{EBO}	V_{EB}=7V; I_c=0			500	uA
Dc current gain	h_{FE}	I_C=5A; V_{CE}=4V;	70		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=4A; I_B=-0.4A			0.5	V
Transition frequency	f_T	V_{CE}=10V; I_{CE}=500mA;f=1MHZ		28		

Symbol	Parameter	Typ	Units
$R_{\theta JC}$	Junction-to-Case	0.68	℃/W

TYPICAL CHARACTERISTICS

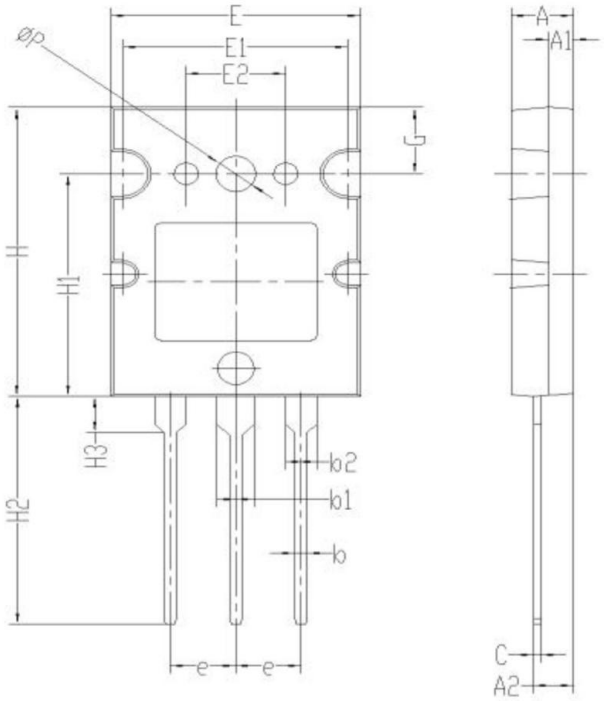
HFE--IC



迈诺斯科技

2SC5200

Package Description



Symbol	Dimensions(millimeters)	
	Min.	Max.
A	4.80	5.20
A1	1.80	2.20
A2	3.00	3.40
b	0.80	1.20
b1	2.80	3.20
b2	2.30	2.70
c	0.40	0.80
e	5.25	5.65
E	19.80	20.20
E1	17.80	18.20
E2	7.80	8.20
H	25.80	26.20
H1	19.80	20.20
H2	20.00	21.00
H3	3.05	3.45
G	5.80	6.20
ΦP	3.10	3.50
J	4.80	5.20
K	1.80	2.20

TO-3PL Package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. BJT is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change withoutprior notice.

CONTACT:

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